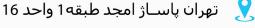






02166766957 -02166766927





info@atrinelec.com



@atrinelec











FMH16N50ES

FUJI POWER MOSFET

Super FAP-E^{3S} series

N-CHANNEL SILICON POWER MOSFET

■ Features

Maintains both low power loss and low noise Lower $R_{DS}(on)$ characteristic More controllable switching dv/dt by gate resistance Smaller V_{GS} ringing waveform during switching Narrow band of the gate threshold voltage (4.2±0.5V) High avalanche durability

Applications

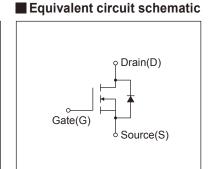
Switching regulators UPS (Uninterruptible Power Supply) DC-DC converters

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings at Tc=25°C (unless otherwise specified)

TO-3P (Q) 15.5m 13.8.2 10.9.2 1.624 1.624 2.224 3.5,5m 5.5,5m 5.5,5m	4,5 st.2 1,5 st.2 0,5 %2	97.2 to 2
+ + + ① ② ③		CONNECTION ① BASE ② COLLECTOR ③ EMITTER EIAJ: SC-65

■ Outline Drawings [mm]



Description	Symbol	Characteristics	Unit	Remarks	
Drain Sauras Valtara	V _{DS}	500	V		
Drain-Source Voltage	V _{DSX}	500	V	V _{GS} = -30V	
Continuous Drain Current	In	±16	Α		
Pulsed Drain Current	IDP	±64	Α		
Gate-Source Voltage	V _G s	±30	V		
Repetitive and Non-Repetitive Maximum Avalanche Current	Iar	16	Α	Note*1	
Non-Repetitive Maximum Avalanche Energy	Eas	485	mJ	Note*2	
Repetitive Maximum Avalanche Energy	Ear	19.5	mJ	Note*3	
Peak Diode Recovery dV/dt	dV/dt	4.8	kV/μs	Note*4	
Peak Diode Recovery -di/dt	-di/dt	100	A/µs	Note*5	
Maximum Power Dissipation	Po	2.50	10/	Ta=25°C	
		195	W	Tc=25°C	
0	Tch	150	°C		
Operating and Storage Temperature range	T _{stq}	-55 to + 150	°C		

● Electrical Characteristics at Tc=25°C (unless otherwise specified)

Description	Symbol	Conditions		min.	typ.	max.	Unit	
Drain-Source Breakdown Voltage	BVDSS	I _D =250μA, V _{GS} =0V		500	-	-	V	
Gate Threshold Voltage	V _{GS} (th)	I _D =250µA, V _{DS} =V _{GS}		3.7	4.2	4.7	V	
Zero Gate Voltage Drain Current		V _{DS} =500V, V _{GS} =0V	T _{ch} =25°C	-	-	25		
	IDSS	V _{DS} =400V, V _{GS} =0V	T _{ch} =125°C	-	-	250	μA	
Gate-Source Leakage Current	Igss	V _{GS} =±30V, V _{DS} =0V	V _{GS} =±30V, V _{DS} =0V		10	100	nA	
Drain-Source On-State Resistance	Ros (on)	I _D =8A, V _{GS} =10V		-	0.33	0.38	Ω	
Forward Transconductance	g _{fs}	I _D =8A, V _{DS} =25V		5.5	11	-	S	
Input Capacitance	Ciss	V _{DS} =25V V _{GS} =0V f=1MHz		-	1700	2550	pF	
Output Capacitance	Coss			-	210	315		
Reverse Transfer Capacitance	Crss			-	13	19.5		
Turn-On Time Turn-Off Time	td(on)	V _{cc} =300V V _{GS} =10V I _D =8A R _{GS} =18Ω		-	37	55.5	ns	
	tr			-	30	45		
	td(off)			-	87	130.5		
	tf			-	17	25.5		
Total Gate Charge	Q _G	V _{cc} =250V I _D =16A V _{es} =10V		-	48	72		
Gate-Source Charge	Q _{GS}			-	17	25.5	nC	
Gate-Drain Charge	Q _{GD}			-	18	27		
Gate-Drain Crossover Charge	Qsw			-	7	10.5		
Avalanche Capability	lav	L=1.52mH, Tch=25°C		16	-	-	Α	
Diode Forward On-Voltage	V _{SD}	I _F =16A, V _{GS} =0V, T _{ch} =25°C		-	0.90	1.35	V	
Reverse Recovery Time	trr	I _F =16A, V _{GS} =0V		-	0.46	-	μs	
Reverse Recovery Charge	Qrr	-di/dt=100A/µs, Tch=25	C	-	6.0	-	μC	

Thermal Characteristics

Description	Symbol	Test Conditions	min.	typ.	max.	Unit
Thermal resistance	Rth (ch-c)	Channel to Case			0.641	°C/W
	Rth (ch-a)	Channel to Ambient			50.0	°C/W

Note *1 : Tch≤150°C

Note *2 : Stating Tch=25°C, I_{AS}=7A, L=18.1mH, Vcc=50V, R_G=50Ω.

EAS limited by maximum channel temperature and avalanche current.

See to 'Avalanche Energy' graph.

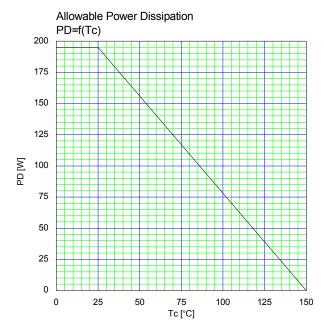
Note *3 : Repetitive rating : Pulse width limited by maximum channel temperature.

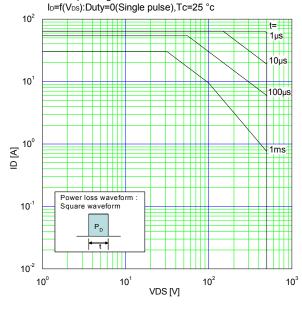
See to the 'Transient Themal impeadance' graph.

Note *4 : Ir≤-I_D, -di/dt=100A/µs, Vcc≤BV_{DS}s, Tch≤150°C.

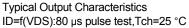
Note *5 : Ir≤-I_D, dv/dt=4.8kV/µs, Vcc≤B_{VDS}s, Tch≤150°C.

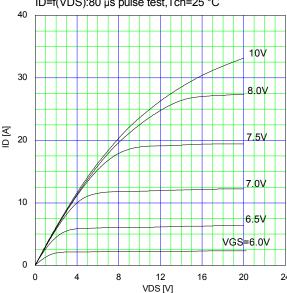
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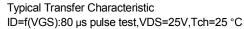


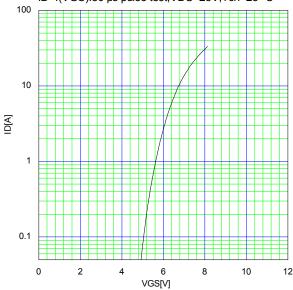


Safe Operating Area

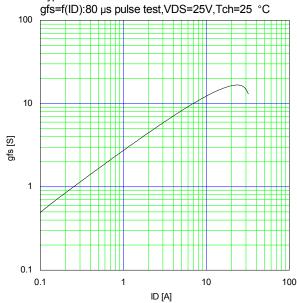




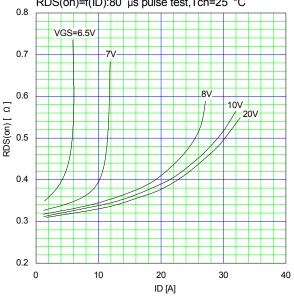




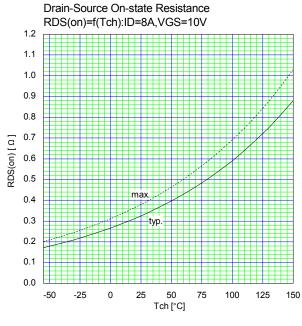
Typical Transconductance

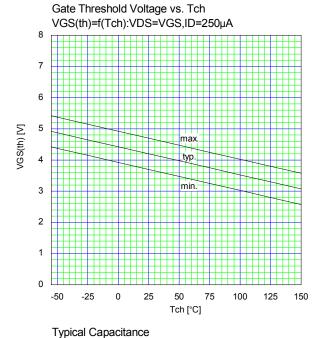


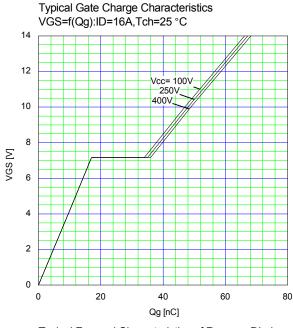
Typical Drain-Source on-state Resistance RDS(on)=f(ID):80 µs pulse test,Tch=25 °C

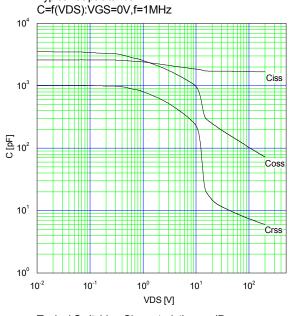


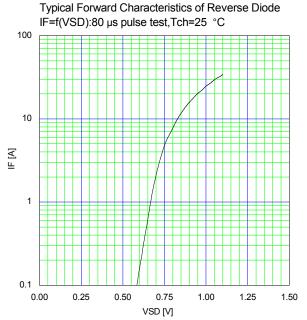
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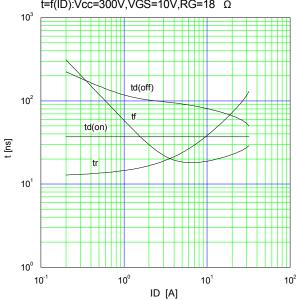


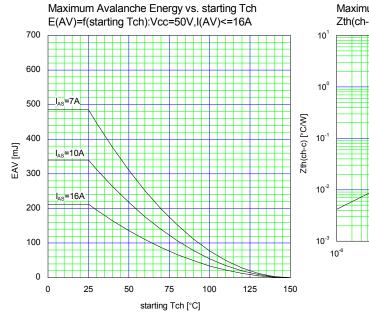














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- Measurement equipment

- Machine tools
- Audiovisual equipment
- Electrical home appliances
- Personal equipment
- Industrial robots etc.
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· Aeronautic equipment

Safety devices

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